

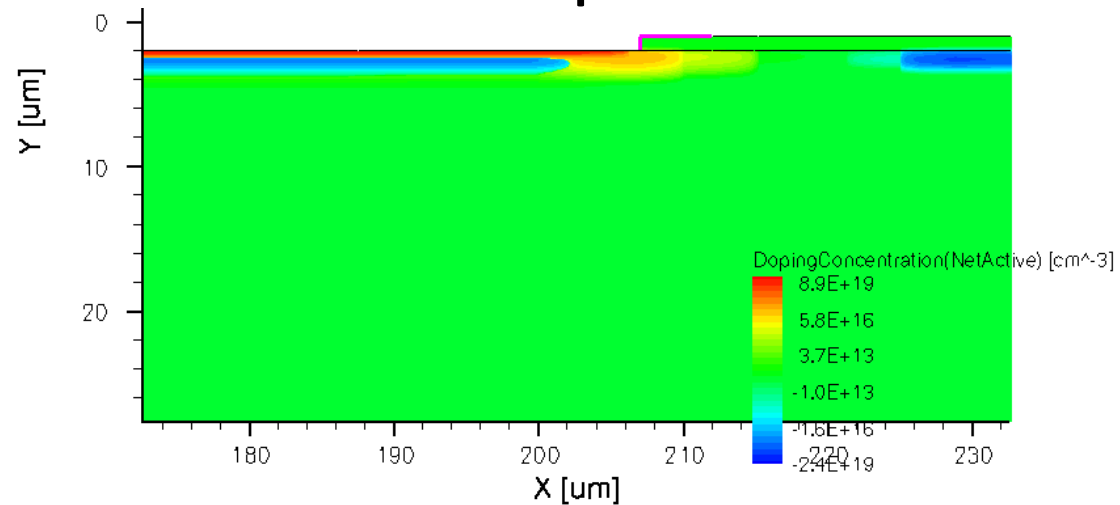
Simulation

Mei Zhao

2018.10.25

Simulation

- Model built based on process



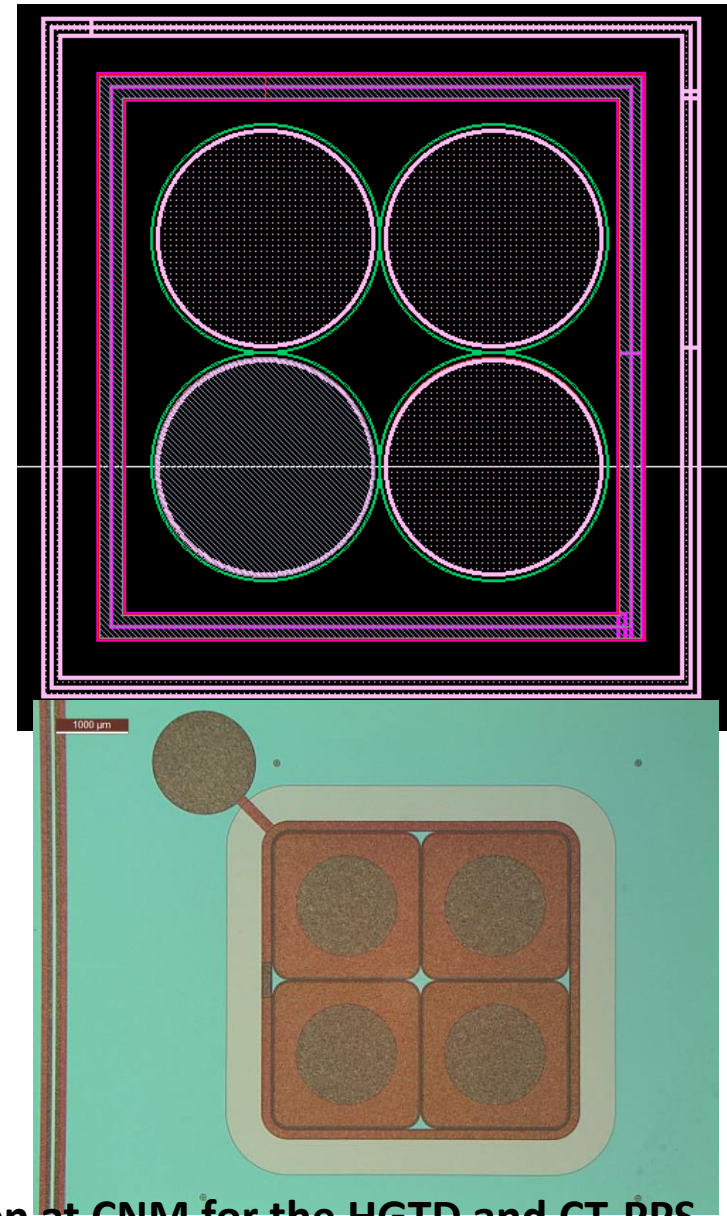
- Simulation of the characteristic

Layout

Size: 1.3mm

Major: Single

- JTE width: 5 μ m, 10 μ m, 15 μ m
- Space between JTE and Pstop
15, 20, 30 μ m
- Field plate
Polysilicon
- Channel stop
- Shape:
Square with round corner
Circle



First 50mm thick LGAD fabrication at CNM for the HGTD and CT-PPS
June 7th 2016, 28th RD50 Workshop, Torino

Process

Mask: 6

- 1、 JTE
- 2、 P layer implantation
Boron, 100keV, $1.8e13cm^{-2}$
- 3、 p stop
- 4、 Channel stop
- 5、 n+ layer
- 6、 field plate deposition, etch
- 7、 p+ back

